





Replaces DS6151-3

Phase Control Thyristor

DS6151-4	March 2022	(LN41616)
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FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
DCR5900A28 DCR5900A26 DCR5900A24	2800 2600 2400	$T_{vj} = -40^{\circ}C \text{ to } 125^{\circ}C,$ IDRM = IRRM = 300mA, $VDRM, VRRM t_{P} = 10ms$ VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5900A28

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

Vdrm	2800V
T(AV)	5750A
тѕм	77000A
dV/dt*	2000V/µs
dl/dt	500A/µs

KEY PARAMETERS

* Higher dV/dt selections are available on request

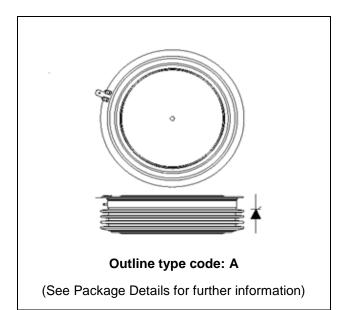


Fig. 1 Package outline

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	5750	А
It(rms)	RMS value	-	9030	А
Іт	Continuous (direct) on-state current	-	7720	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	77.0	kA
l²t	I ² t for fusing	VR = 0	29.6	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditior	Min.	Max.	Units	
		Double side cooled	DC	-	6.0	°C/kW
Rth(j-c)	Thermal resistance - junction to case		Anode DC	-	10.4	°C/kW
		Single side cooled	Cathode DC	-	14.9	°Ck/W
Balan	Thermal registeres access to heateink	Clamping force 83kN	Double side	-	1.0	°Ck/W
Ktn(c−n)	Rth(c-h) Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	2.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			74	91	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditior	IS	Тур.	Max.	Units
	Deck manage and aff state armout	At Vrrm/Vdrm, Tcase = 125°C		-	300	mA
Irrm/Idrm	Peak reverse and off-state current	At 50% VRRM/VDRM, Tcase = 7	125°C	20	-	mA
Symbol	Parameter	Test Conditior	IS	Min.	Max.	Units
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.07	1.15	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrm, Tj = 125°С, g	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x IT(AV) Gate source 30V, 10Ω	Repetitive 50Hz	-	250	A/µs
		tr < 0.5µs, Tj = 125°C	Non-repetitive	-	500	A/µs
V	Threshold voltage - Low level	500A to 3500A at T _{case} = 125°C		-	0.77	V
V τ(το)	Threshold voltage - High level	3500A to 8000A at Tcase = 125°C		-	0.91	V
-	On-state slope resistance - Low level	500A to 3500A at T _{case} = 125°C		-	0.10	mΩ
ľτ	On-state slope resistance - High level	3500A to 8000A at Tcase = 1	25°C	-	0.06	mΩ
tgd	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω tr = 0.5µs, Tj = 25°C		-	3	μs
tq	Turn-off time	Iτ = 5000A, Tj = 125°C, V _R = 200V, dl/dt = 5A/μs, dV _{DR} /dt = 20V/μs linear		-	250	μs
Qs	Stored charge	Iτ = 1600A, Tj = 125°C, dl/dt = 1A/μs		1560	4950	μC
Irr	Reverse recovery current	VR ~ 1100V, Cs = 1μF, Rs = 63Ω		30	62	А
L	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ін	Holding current	Тј = 25°С, Rg-к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgт	Gate trigger voltage	Vdrм = 5V, Tcase = 25°С	1.5	V
Vgd	Gate non-trigger voltage	At 50% Vdrm, Tcase = 125°C	0.4	V
Іст	Gate trigger current	Vdrм = 5V, Tcase = 25°С	400	mA
Igd	Gate non-trigger current	At 50% Vdrм, Tcase = 125°С	10	mA

CURVES

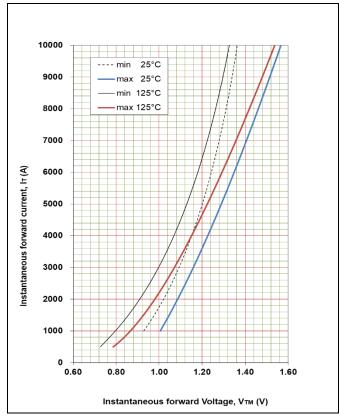


Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

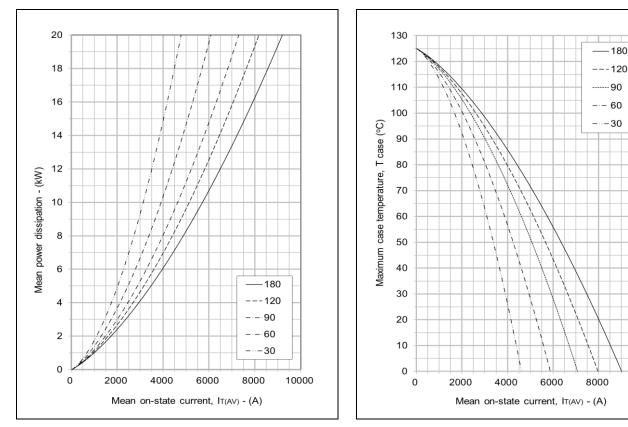
Where A = 0.502193 B = 0.024599 C = 0.000029 D = 0.005189 These values are valid for $T_j = 125^{\circ}C$ for IT 500A to 8000A

DCR5900A28

180

90

10000



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Fig. 3 On-state power dissipation - sine wave

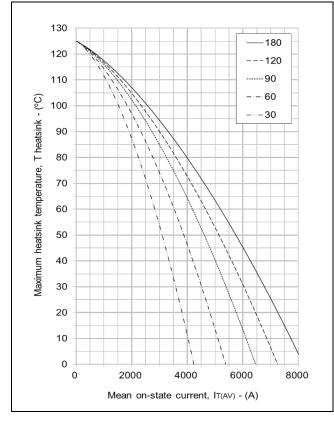


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

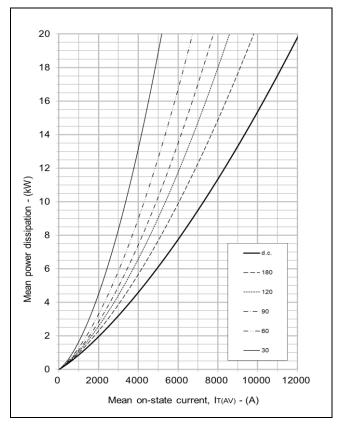


Fig. 6 On-state power dissipation - rectangular wave

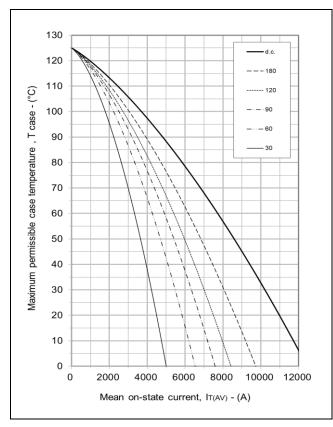
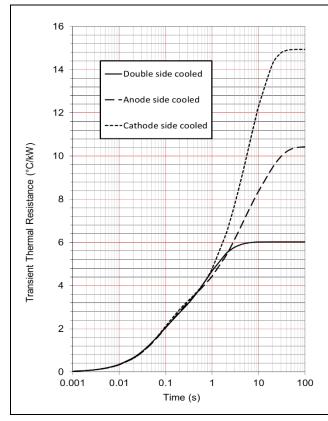


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



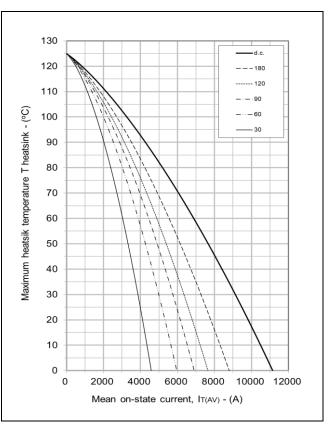


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	3.015	1.049	0.984	0.984
cooled	Ti(s)	0.704	1.905	0.059	0.059
Anode side cooled	Ri(°C/kW)	3.156	4.093	1.557	1.624
	Ti(s)	2.690	13.792	0.059	0.206
Cathode side	Ri(°C/kW)	7.077	3.483	1.746	2.634
cooled	Ti(s)	6.649	8.436	1.762	0.081

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{th(j-c)}$ Conduction

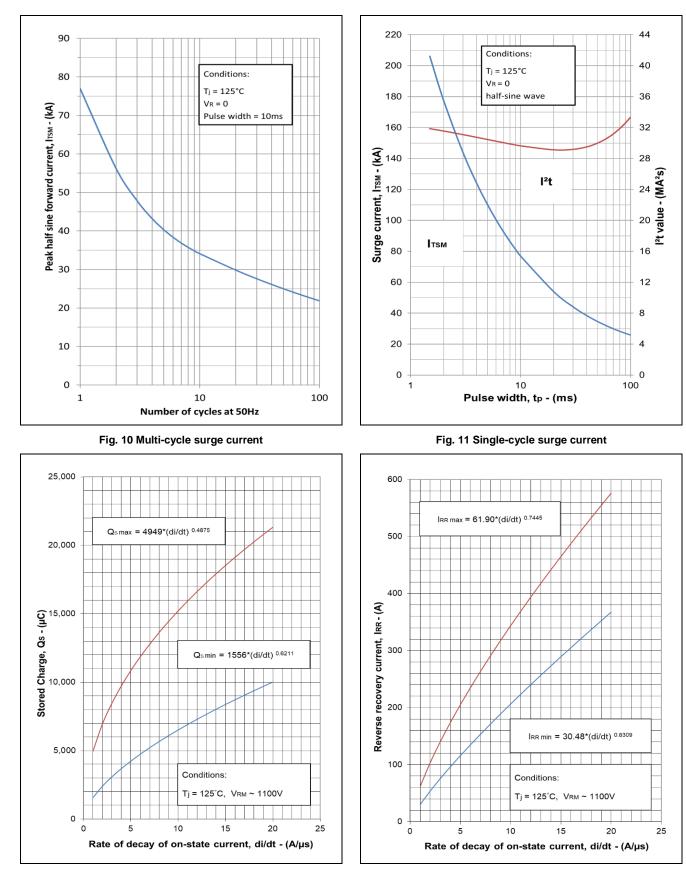
Tables show the increments of thermal resistance R $_{\text{frij-ej}}$ when the device operates at conduction angles other than d.c.

Double side cooling			Anode Side Coolin			Cath	ode Side	ed Cooling
ΔZ_{th}	(z)		ΔZ	_{th} (z)			ΔZ	th (z)
sine.	rect.	θ°	sine.	rect.		θ°	sine.	rect.
0.44	0.31	180	0.42	0.30	1	180	0.42	0.30
0.49	0.43	120	0.47	0.41	ÍÍ	120	0.47	0.41
0.55	0.49	90	0.52	0.46	1	90	0.52	0.46
0.60	0.55	60	0.57	0.52	I [60	0.57	0.52
0.64	0.61	30	0.61	0.58	ΙΙ	30	0.60	0.58
0.66	0.64	15	0.62	0.61	1 [15	0.62	0.60
	ΔZ _{th} sine. 0.44 0.49 0.55 0.60 0.64	ΔZ _{th} (z) sine. rect. 0.44 0.31 0.49 0.43 0.55 0.49 0.60 0.55 0.64 0.61	$\begin{array}{c c} & & & & \\ & & & \\ \hline Sine. & rect. & \\ \hline 0.44 & 0.31 & \\ 0.49 & 0.43 & \\ 0.55 & 0.49 & \\ 0.60 & 0.55 & \\ \hline 0.64 & 0.61 & \\ \hline \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Fig.9 Maximum (limit) transient thermal impedance – junction to case (degC/kW)

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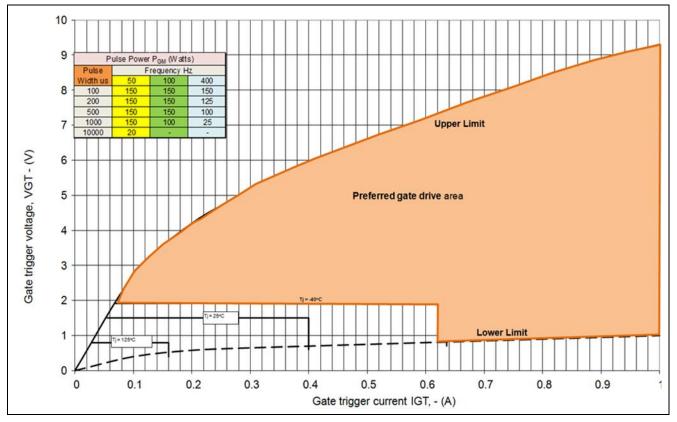
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Fig. 12 Stored charge

Fig. 13 Reverse recovery current



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Fig.14 Gate characteristics

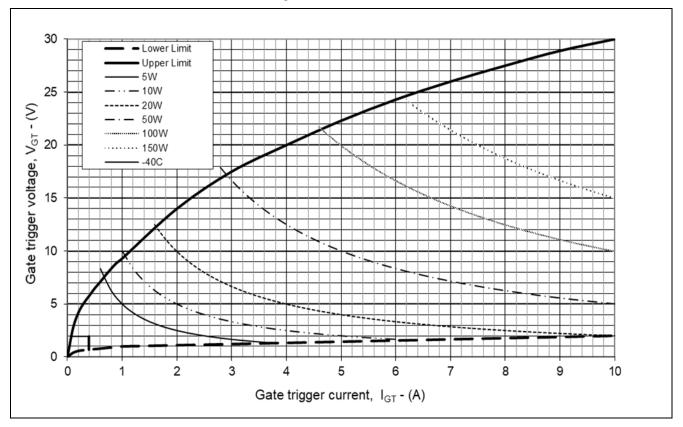


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

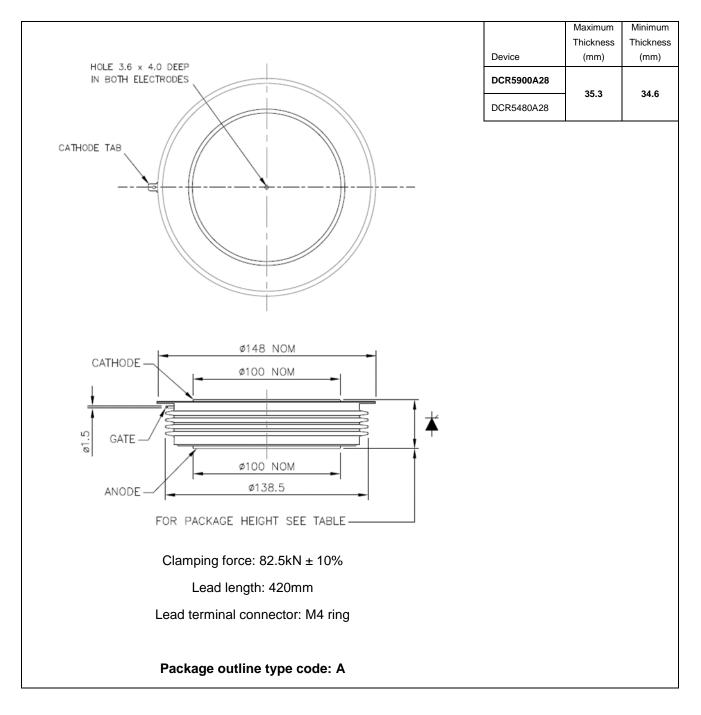


Fig. 16 Package outline

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